

Error attribution for singlet-triplet qubits through randomized benchmarking in the presence of temporally correlated noise

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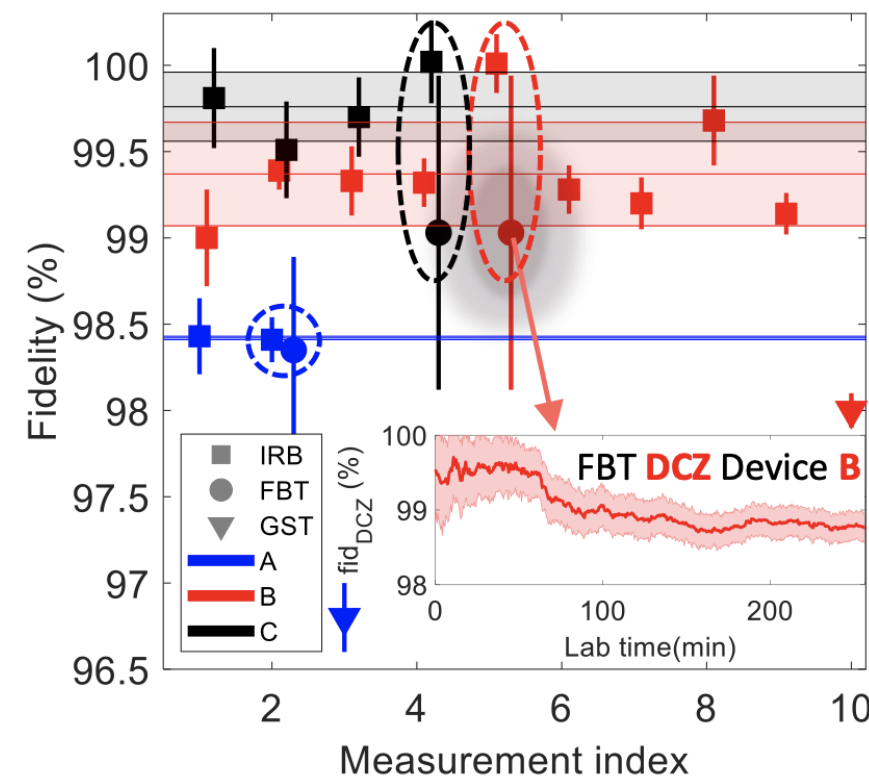
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Problem statement

- Qubit fidelity can drift under noisy lab conditions
 - Correlated charge and magnetic noise present
- **Randomized benchmarking (RB) is used to quantify qubit fidelity over time**
 - Apply L Clifford operators + inverse
- **Can we simulate drift and use comparison with experiment to learn more about the noise itself or stress test our error models?**
 - ‘Wall-clock’ simulations: replicate laboratory conditions over complete RB experiments
 - **Maintain correlations in background noise over long timescales**
 - Efficient simulations allowing for ‘fast-forwarding’ of noise

Example of drift from Dzurak group (UNSW)

(a) Fidelities from different measurements



[Tanttu, et al. arXiv:2303.04090 (2023)]

System of interest

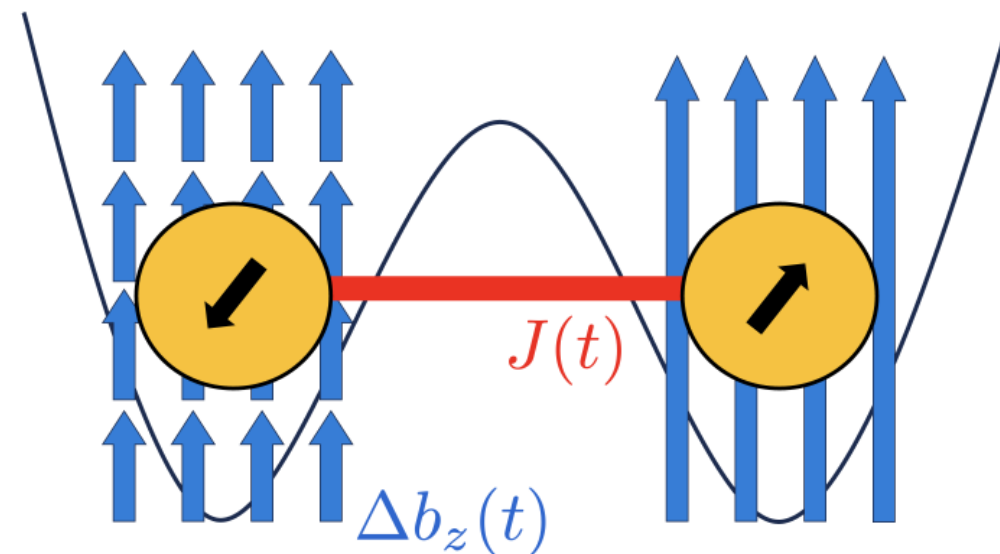
- Single qubit in the singlet-triplet encoding
- Hamiltonian:

$$H_{ST_0}(t) = \underbrace{J_0 e^{\alpha(V_0(t) + \delta V(t))}}_{\text{Exchange Coupling: } J(t)} S^z + \underbrace{(\Delta b_z + \delta b_z(t))}_{\text{Hyperfine Splitting: } \Delta b_z(t)} S^x$$

Voltage Noise Magnetic Noise

- Exchange coupling is a function of voltage
- **Temporally correlated voltage and magnetic noise generate classical Hamiltonian noise**
- Unitaries are approximated as

$$U(T) \approx \prod_{k=1}^{T/\Delta t} \exp \left[-\frac{i \overbrace{\Delta t}^{\text{Sampling time } (\Delta t \sim 1\text{ns})}}{\hbar} H_{ST_0}(k\Delta t) \right]$$



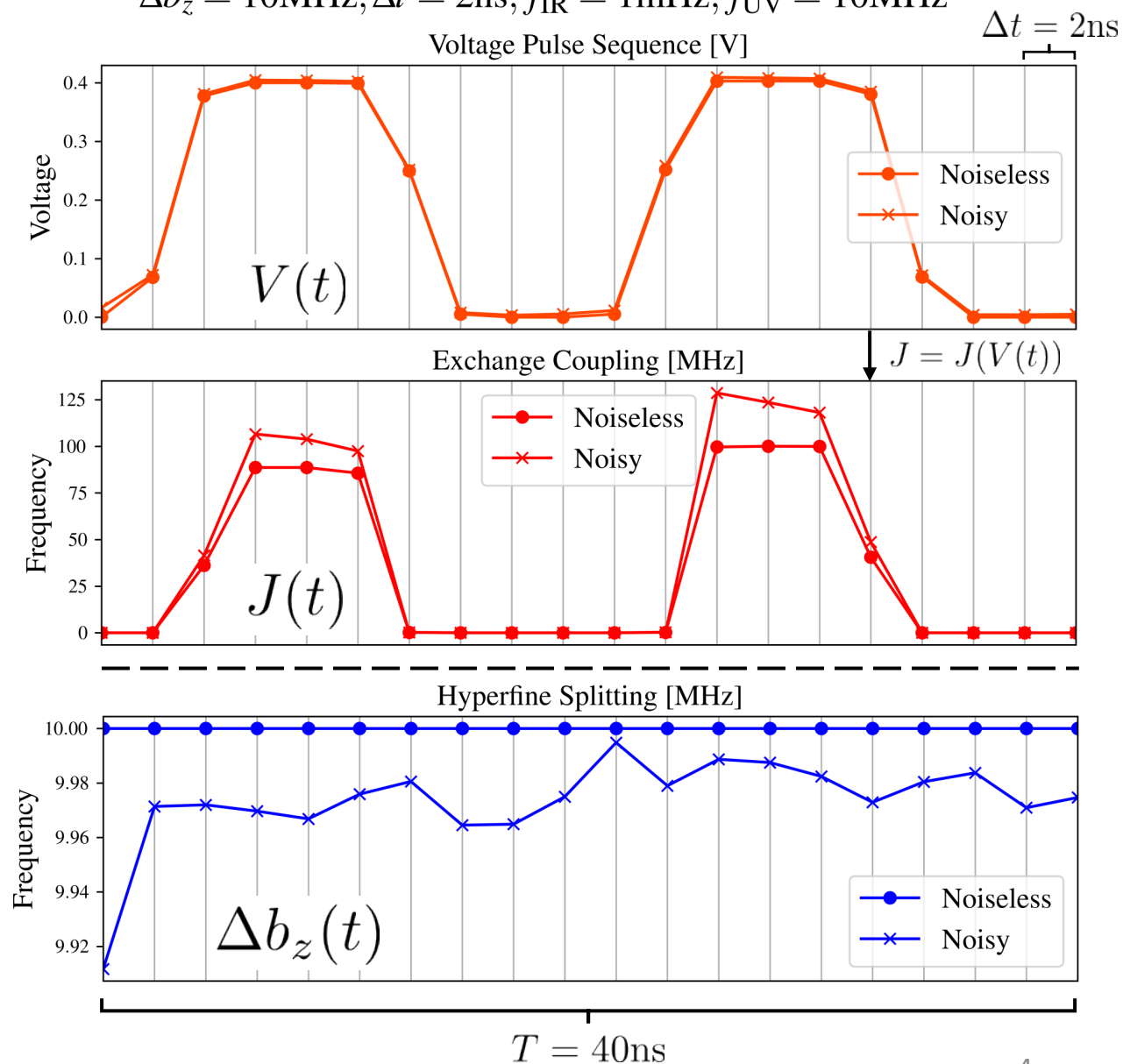
Generating voltage pulses

- Realistic voltage pulse timings are optimized to generate Clifford operators C_i
 - Objective function: maximize fidelity of approximated unitary with respect to target Clifford

$$\max \left(\frac{1}{4} \left| \text{Tr} \left[C_i^\dagger U(V_0(t), \Delta b_z) \right] \right|^2 \right)$$

- Pulse durations, rise/decay times, sampling times, etc. replicate pulses created by waveform generators
- Environment parameters also adjustable

Sample Clifford Pulse Sequence
 $C_6 = X(-\pi/2)Z(-\pi/2)X(\pi/2)Z(\pi/2)$
 $\Delta b_z = 10\text{MHz}, \Delta t = 2\text{ns}, f_{\text{IR}} = 1\text{mHz}, f_{\text{UV}} = 10\text{MHz}$



Calibrating our noise model

- Correlated noise modeled as a sum of Ornstein-Uhlenbeck processes:

$$S(f) = \sum_j \frac{p_j f_j}{\pi(f^2 + f_j^2)}$$

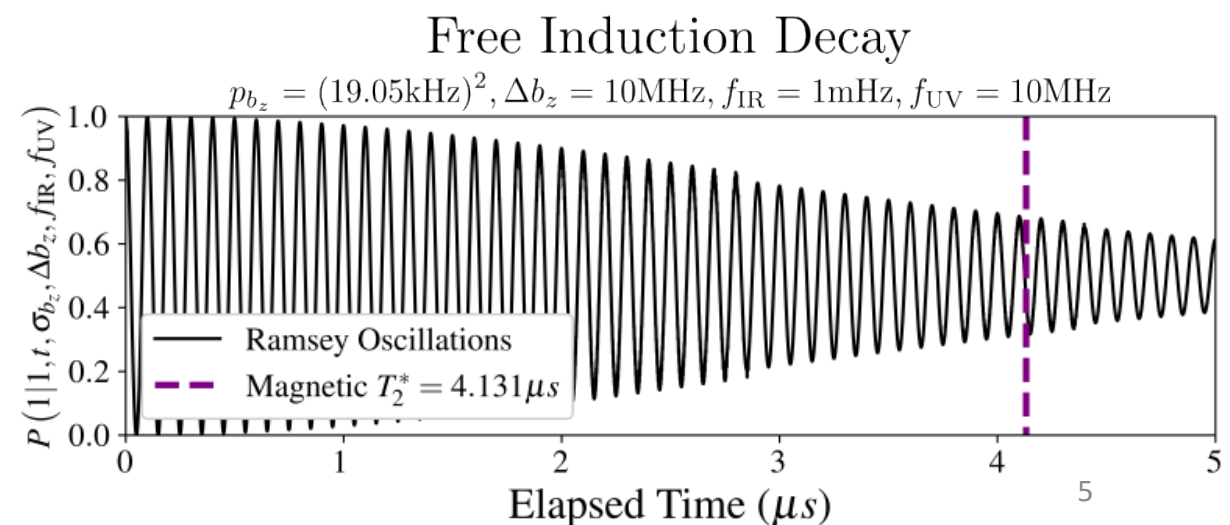
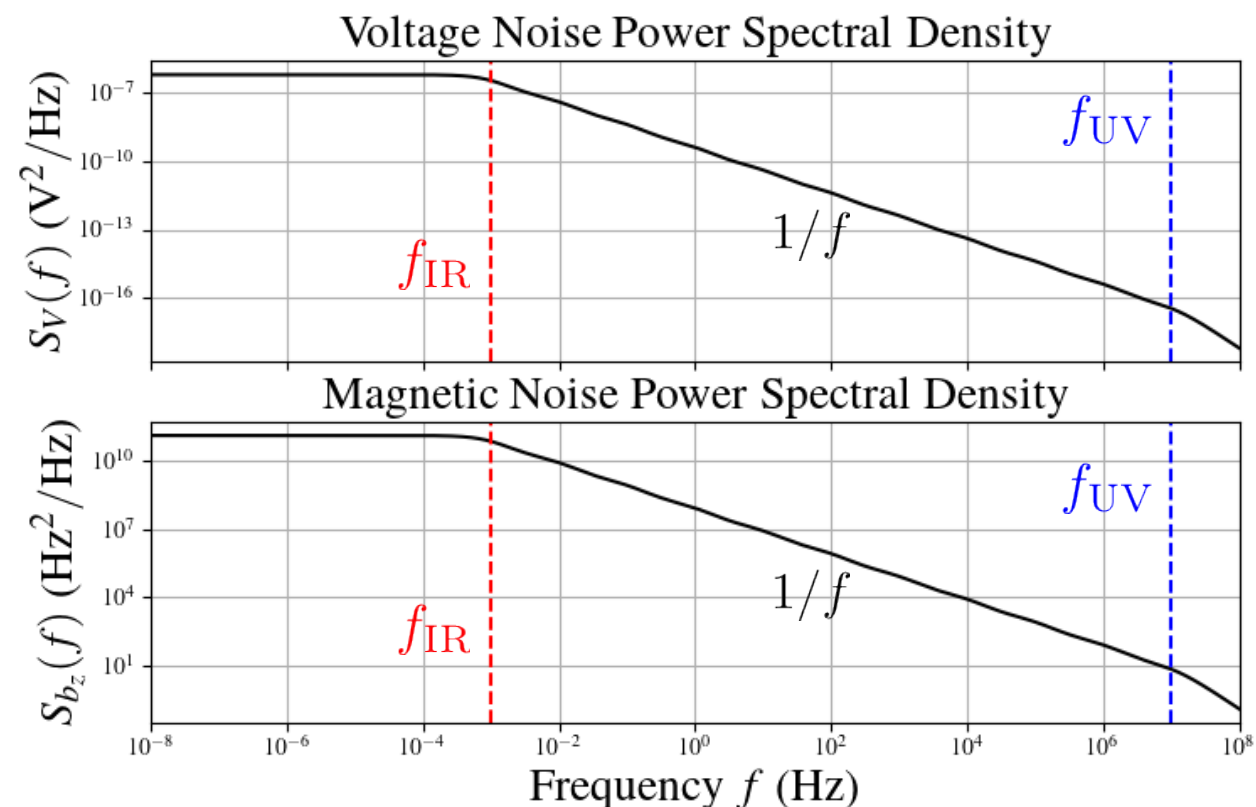
p_j : Process power

f_j : Characteristic process frequency

$$f_{\text{IR}} = \min_j f_j \quad f_{\text{UV}} = \max_j f_j$$

- Used to model $1/f$ power spectral density
- Can efficiently fast-forward noise over arbitrarily large time intervals**
- Sampling frequency sufficiently high such that aliasing effects are negligible
- Magnetic noise process power calibrated by matching simulated T_2^* with device measurement

Informed noise model mirrors in-lab conditions



Simulated randomized benchmarking schematic

Time $t \longrightarrow$

* Depicted SPAM times are not to scale.

Initialize Noise

Randomized Benchmarking (Single Pass)

Depth L_1

Depth L_2

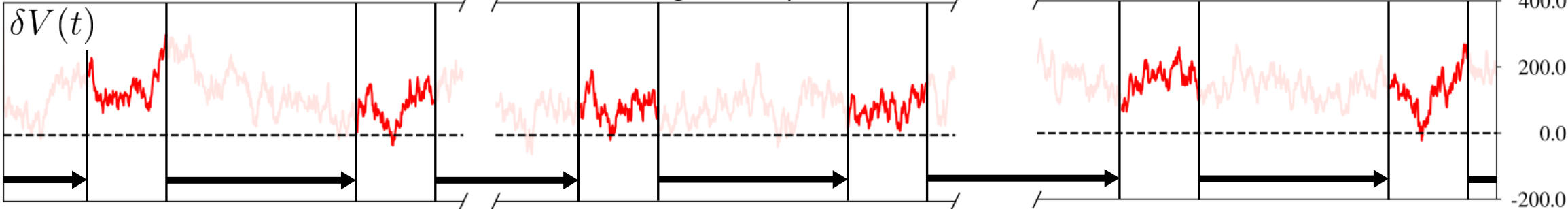
Classical Sequence $C_1^{L_1}$

Classical Sequence $C_2^{L_1}$

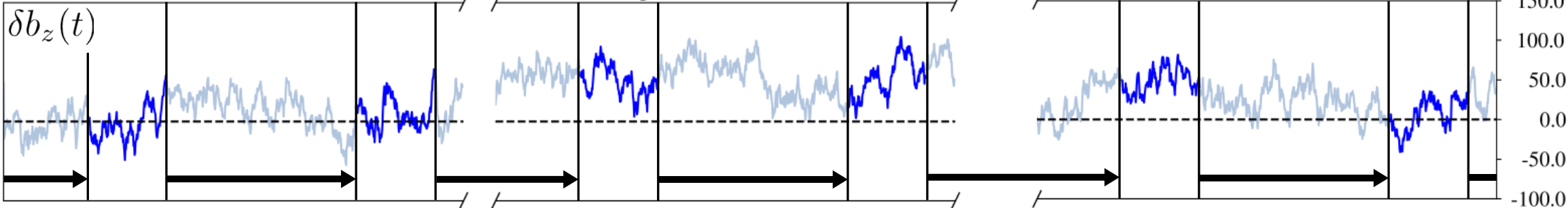
Classical Sequence $C_1^{L_2}$



Voltage Noise [μV]



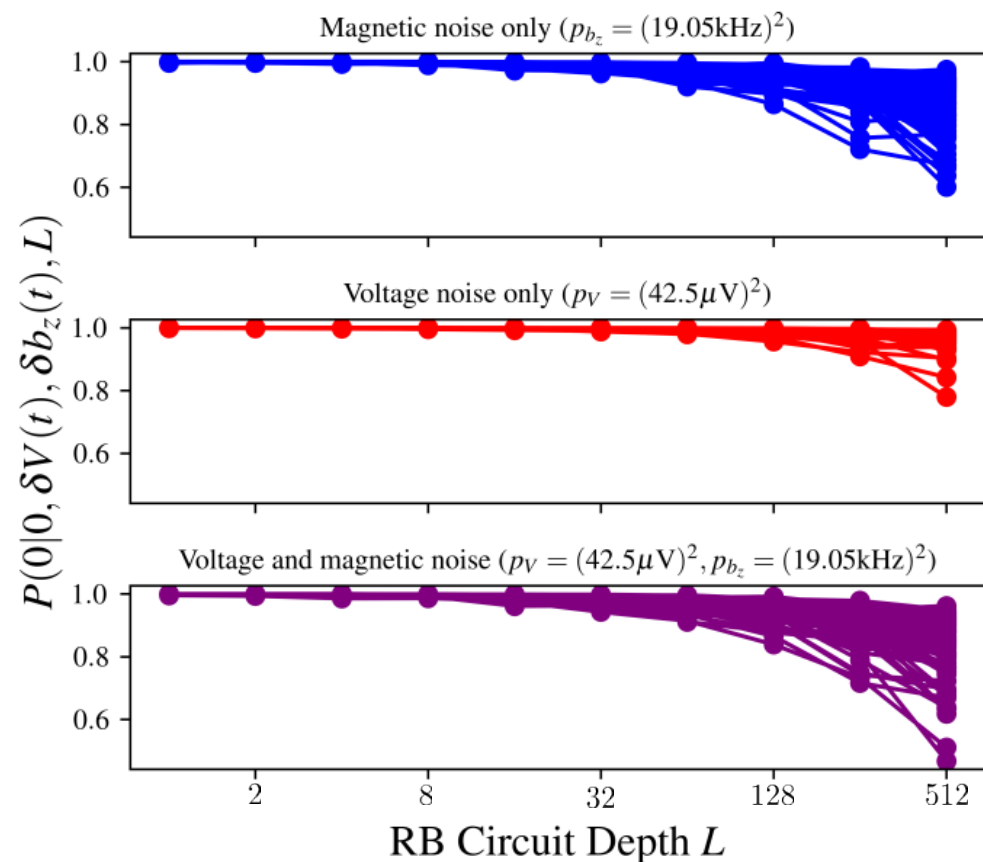
Magnetic Noise [kHz]



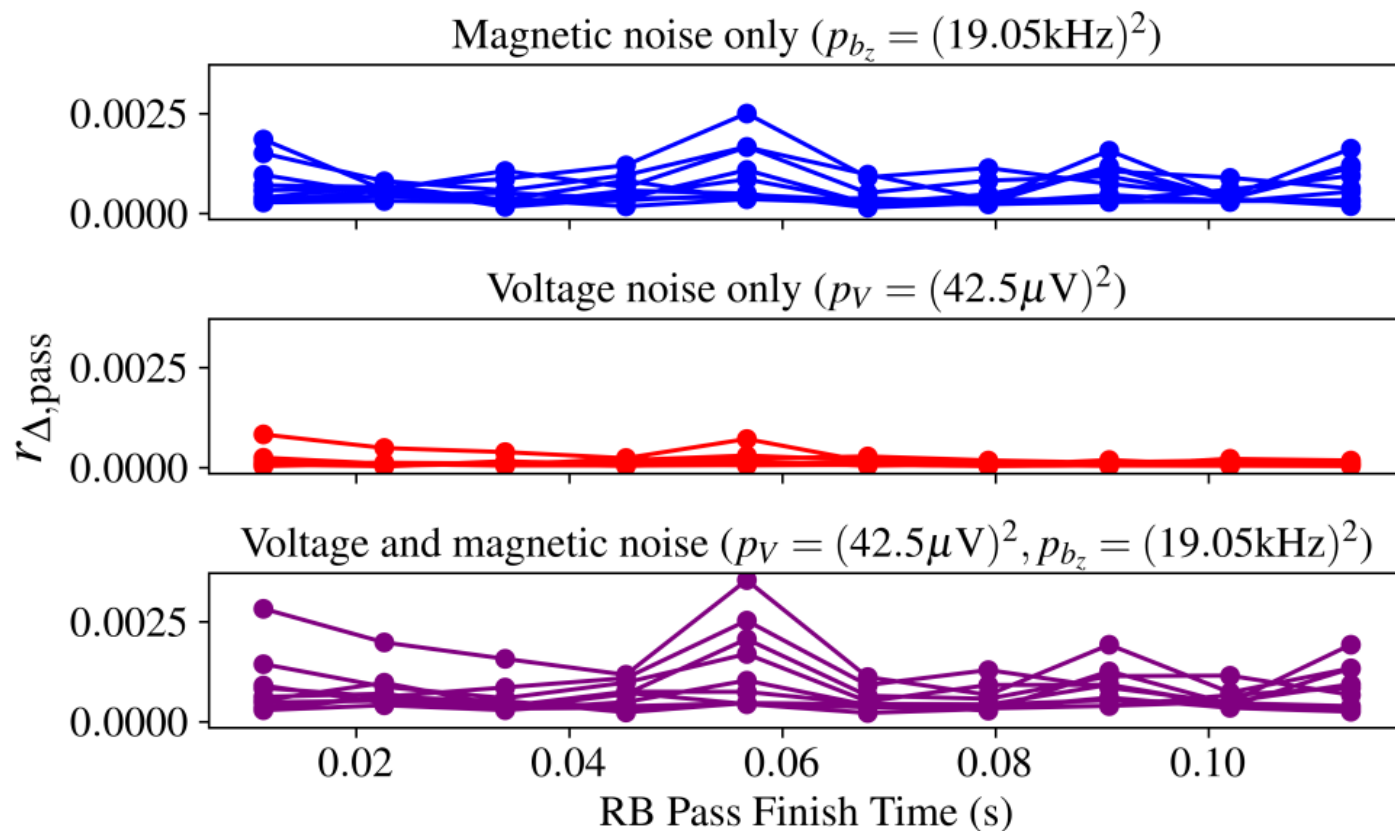
Noise can be efficiently 'fast-forwarded' during SPAM/idling periods

Simulated drift in randomized benchmarking

RB decay curves
(fixed simulation seeds and Clifford sequences)



Approximate per-gate error over time
(fixed simulation seeds and Clifford sequences)



Drift in RB number across several experiments is captured

(Fixed $f_{\text{IR}} = 1\text{mHz}$, $f_{\text{UV}} = 10\text{MHz}$)

Error attribution based on per-circuit bitflip probabilities

- Model for characterizing circuit susceptibility to various noise sources:

$$\hat{P}(1|0, p_V, p_{b_z}, U_i) = \frac{p_V}{\alpha_i^2} + \frac{p_{b_z}}{\beta_i^2}$$

U_i : unique Clifford sequence

α_i, β_i : fit parameters (dependent on U_i)

$(\tilde{p}_V, \tilde{p}_{b_z})$: unknown noise parameters

$(\hat{p}_V, \hat{p}_{b_z})$: inferred noise parameters

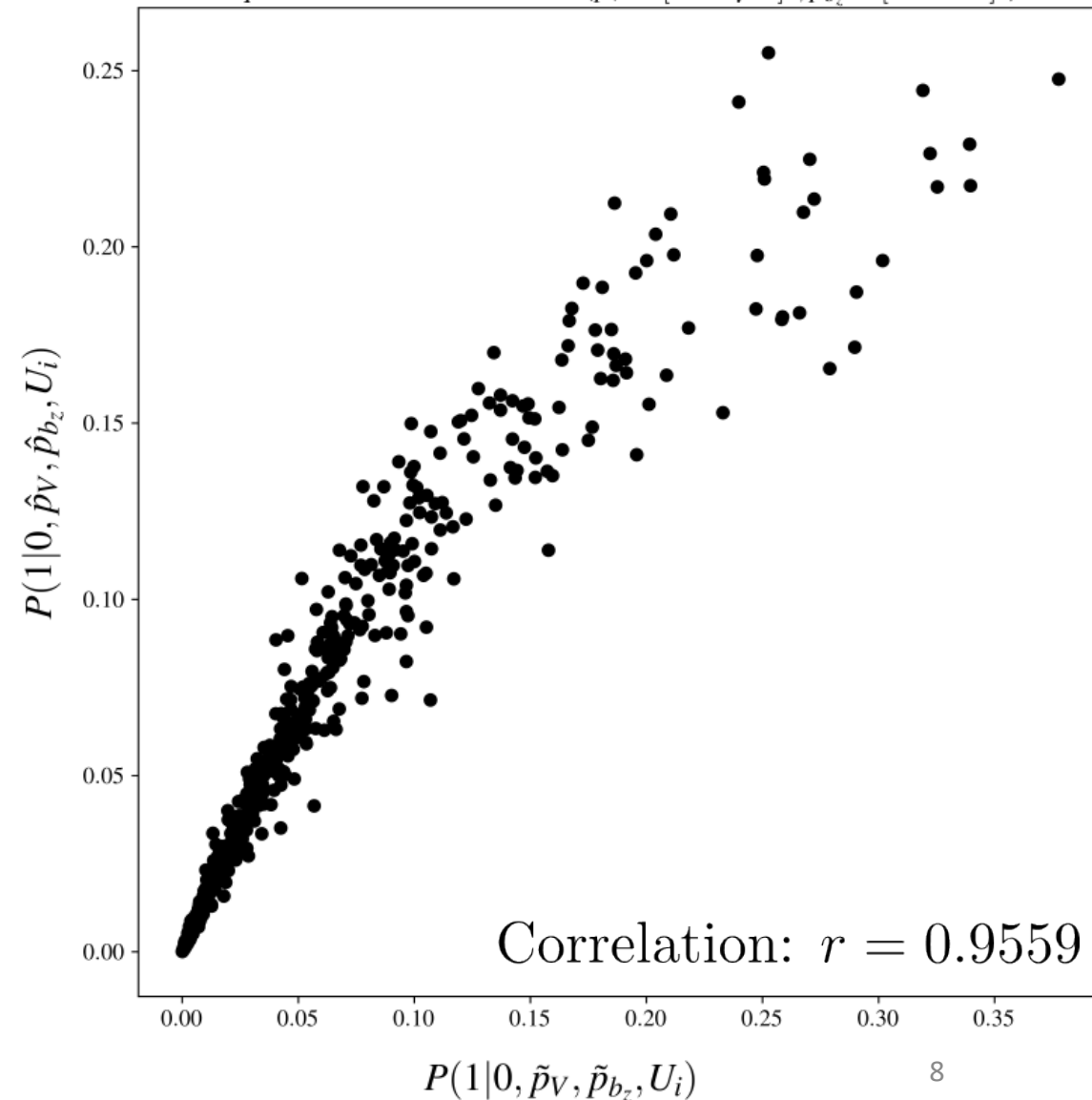
- Noise parameters can be estimated as

$$(\hat{p}_V, \hat{p}_{b_z}) = \arg \min_{(p_V, p_{b_z})} \sum_i \left[\underbrace{P(1|0, \tilde{p}_V, \tilde{p}_{b_z}, U_i)}_{\text{Actual}} - \underbrace{\hat{P}(1|0, p_V, p_{b_z}, U_i)}_{\text{Estimated}} \right]^2$$

Actual vs. predicted bitflip probabilities under inferred noise conditions

$$\tilde{p}_V = [42.5\mu\text{V}]^2, \tilde{p}_{b_z} = [19.05\text{kHz}]^2$$

Square Residual Minimization ($\hat{p}_V = [45.28\mu\text{V}]^2, \hat{p}_{b_z} = [25.0\text{kHz}]^2$)



Model effectively estimates underlying noise parameters

Summary

- Singlet-triplet qubits subject to correlated noise
- **Wall-clock simulations can be used to calibrate circuit-specific bitflip probability estimators**
 - Relative sensitivity of individual Clifford sequences can be deduced from fit parameters
- **Calibrated estimators can be used to infer unknown background noise levels**
- **Developed computationally efficient means to simulate realistic device conditions across several RB experiments (lab time)**
 - Computationally cheap ‘fast-forwarding’ of $1/f$ noise without losing correlations
 - Pulses, noise parameters, etc. tunable to model realistic device/laboratory conditions
 - Can capture the effects of slow drift in noise
- Future work
 - Multi-qubit analysis
 - Alternate qubit encodings (e.g., exchange-only qubit encoding)
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